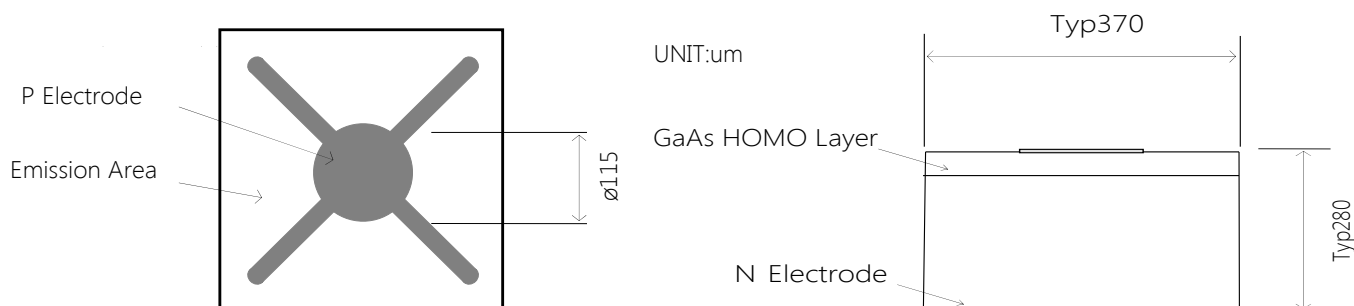


Radiation	Type	Electrodes
Infrared	GaAs	P (anode) up



Physical Characteristics & Structure

Material: GaAs	Bond Pad Size: 115um diameter
Junction Size: 370um x 370um	Anode Metalization: Gold Alloy
Thickness: 280um	Cathode Metalization: Gold Alloy

Electrical & Optical Characteristics (Ta = 25°C)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	Vf	If=20mA	--	--	1.4	V
Reverse Voltage	Vr	Ir=10uA	5	--	--	V
Radiant Power*	Φe	If=20mA	0.4	--	--	mW
Peak Wavelength	λp	If=20mA	--	940	--	nm
Spectral Bandwidth at 50%	Δλ0.5	If=20mA	--	45	--	nm

* LED chip is mounted on TO-18 gold header without resin coating.

Absolute Maximum Ratings (Ta = 25°C)

Continuous Maximum Forward Current: 50mA (DC)
Reverse Voltage: 5V (IR=10uA)
Storage Temperature
while on mylar membrane: 0 to 40 °C
after removal from mylar membrane: -30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

2014-04-24